

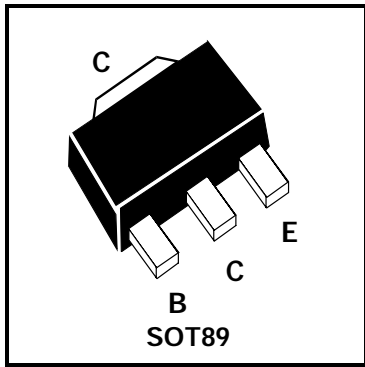
SOT89 NPN SILICON PLANAR DARLINGTON TRANSISTOR

BST52

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FEATURES

- * Fast Switching
- * High h_{FE}



PARTMAKING DETAIL — AS3

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	90	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	10	V
Pea Pulse Current	I_{CM}	1.5	A
Continuous Collector Current	I_C	500	mA
Base Current	I_B	100	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_J:T_{stg}$	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	90		V	$I_C=10\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80		V	$I_C=10\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10		V	$I_E=10\mu\text{A}, I_C=0$
Emitter Cut-Off Current	I_{EBO}		10	μA	$V_{EB}=8\text{V}, I_E=0$
Collector-Emitter Cut-Off Current	I_{CES}		10	μA	$V_{CE}=80\text{V}, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		1.3 1.3	V V	$I_C=500\text{mA}, I_B=0.5\text{mA}$ $I_C=500\text{mA}, I_B=0.5\text{mA}$ $T_J=150^\circ\text{C}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.9	V	$I_C=500\text{mA}, I_B=0.5\text{mA}$
Static Forward Current Transfer Ratio	h_{FE}	1K 2K			$I_C=150\text{mA}, V_{CE}=10\text{V}^*$ $I_C=-500\text{mA}, V_{CE}=-10\text{V}^*$
Turn On Time	t_{on}	400 Typical		ns	$I_C=500\text{mA}$ $I_{Bon}=I_{Boff}=0.5\text{mA}$
Turn Off Time	t_{off}	1.5K Typical		ns	

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device
For typical characteristics graphs see FMMT614 datasheet.